

# Index

*Italic numbers denote pages with tables and figures.*

- 1SS (single-sequential scattering) 194–5, 197
- 2DEG (two-dimensional electron gas)
  - analytically manageable transport model 458–60
  - and Bloch states 113
  - and the Brillouin zone 113
  - charge control 265–82
    - in a heavily dual pulse-doped MODFET structure 449–58
    - with a Schottky junction 272–5
  - equilibrium population 269–72
  - full channel sheet resistance 529, 574
  - pinch-off voltage 274–5
  - population as a function of the Fermi energy 265–9
  - and quantum wells 110–15, 265–6
  - and the Wannier eigenstate equation 265–7
- 68/32% rule 21–3
- AIAs
  - band structure 15
  - bandgap, lattice parameter and electron affinity 20
  - material parameters 3
- AlSb
  - band structure 15
  - bandgap, lattice parameter and electron affinity 20
- $\text{Al}_m\text{Ga}_{1-m}\text{As}$  300 K parameters 47
- abrupt heterojunction 29–31, 34
  - band diagram 30, 39
  - and HBTs 45
- accelerated band electron 98–106
  - Bloch oscillator 104–5
  - Stark states and the Wannier ladder 98–102, 105
  - time-dependent solutions and the Houston state 102–4, 105–6
- acceleration theorem in a crystal 104
- acoustic phonon deformation potential scattering 162–4
  - interaction potential 164
- Agilent EEsof Root FET Model, gate resistance 533
- Airy function 109
- AlGaAs models with silicon doping 25, 455–6
- alloy scattering 21, 169–72, 206–7
- alloys, semiconductor 20–3
  - virtual-crystal approximation 20
- Anderson band-diagram model 26–8, 29, 30
- Anderson localization 135
- AUDM (advanced unified defect model), 551, 552, 535, 554–6
- avalanche breakdown, short-gate MODFETs 471–2
- backscattering
  - and electron–electron scattering 174
  - and scattering assisted tunneling 177
- ballistic launching 42–4
  - electron velocity distribution 42, 43
- ballistic transport 177
- band structures
  - band diagrams
    - n–p heterojunction 43
    - valence band edge 38
  - bandgap various semiconductors 20
  - discontinuity differences 23
  - equilibrium band diagrams 26–8
  - and the reciprocal lattice 11–14
  - and Vegard’s law 21
- bandgap engineering 5–7
- Bardeen’s method 543–4
- barrier height, and interface roughness scattering 165–6
- beryllium diffusion reliability problem for HBTs 670–4
- Bloch equation/function/theorem/state
  - and electron in a periodic potential 57–8
  - and the Houston state 102, 105–6, 223–6
  - and interface roughness scattering 166
  - three-dimensional 67
  - and Wannier functions 60, 64
- Bloch oscillator 104–5
  - and superlattices 132–3
- Boltzmann equations/function 34, 287–90, 627
  - Boltzmann transport equation (BTE), direct solution 614–24
  - and Bose–Einstein distribution 290
  - and electron transport in
    - high electric fields 294–9
    - small electric fields 290–2
  - Maxwell–Boltzmann distribution 287–9
- Bose–Einstein distribution
  - and the Boltzmann equation 290
  - and phonons 156–7, 205
- Brag reflections 13
- Bravais cell 8, 9, 10, 65
  - and alloy scattering 172
- Brillouin zone 10–11, 13–14, 15, 58
- BTE *see* Boltzmann equations/function
- C–V characteristics 275–9, 279–81
  - microwave measurements 247–50

- CAD (computer aided design) models 445–6, 480  
capacitances  
  MODFETs, channel current continuity equation 460–1  
  MODFETs, short gate, capacitance calculations 520, 496–507  
  RTDs 238–41  
chordal mobility 299  
circuit simulations *see* modeling  
conductances  
  drain conductance 335  
  effective noise conductance 594  
  maximum transconductance 343, 476  
  open-channel conductance 490–1  
  output conductance 514, 572–3  
  RTDs 237–8  
conservation of energy and momentum, for phonons 153  
conservation equation 72  
contact resistances, MODFETs 464–7  
Coulomb interaction potential 172  
coulombic potential 280  
coupling functions, scattering processes 204–7  
Cowley–Sze picture 534–8, 540, 546, 551–2, 554  
crystals and lattice structures 8–14  
  Bravais cell 8, 9  
  crystal vibrations 12–13  
  lattice parameter various semiconductors 20  
  as networks of masses and strings 148–9  
  reciprocal lattice 9–11, 11–14  
  scattering analysis 150–1  
  vibrations by crystal Hamiltonian 150  
  zinc-blende structure 8–11  
  
DBS (direct broadcast satellite) applications and FET noise 593  
DC modeling 446–8  
DDE(drift diffusion equation)-based simulators 627–9  
Debye length 24, 267  
deformation potential phonon scattering 162–4, 205–6  
device characterization 415–20  
  DC  $I$ – $V$ – $T$  of an LD MOSFET 416  
  isothermal  $I$ – $V$  418–19  
  methods and problems 415  
  pulsed  $I$ – $V$  416–17, 418  
DHBT (double-heterojunction bipolar transistor) 655–6  
DIGS (disorder-induced gap state) model 535, 536, 538, 556  
doping  
  and the HBT 45  
  *see also* modulation doping  
double-barrier system/structure  
  and Bloch wave of energy 115  
  resonant tunneling 115–19, 179  
  symmetrical 117–19  
  and the Wannier recurrence equation 115–19  
drain (or output) conductance, MODFETs 335, 514–5  
drain resistances, short-gate MODFETs 464–5, 527, 562, 574, 576, 578, 597–9, 602  
drift-diffusion transport model/equations 31–4  
DX trap phenomenon, MODFETs 25, 455–6  
  
Ebers–Moll model large signal HBTs 643–6  
Einstein model, and phonons 152  
Einstein relation 298  
electron affinity 23, 26, 27, 30  
  varous semiconductors 20  
electron particle current  
  conservation equation 72–3  
  definition 72–5  
  flat band case 74–5  
  total particle current 73–4  
electron in a periodic potential 55–8  
  and the Bloch equation/Bloch function 57  
  and eigenvector values 56–7  
  and the translation operator 55–6  
electron transport *see* high electric field electron transport; small electric field electron transport  
electron wave-function 12  
electron–electron interactions 25  
electron–electron scattering 172–4  
  and creation and annihilation operators 173  
electrothermal modeling 433–5  
emission coefficient, and infrared response 256–9  
energy balance equation, high electric field electron transport 295–6  
energy dispersion for photons, free electrons and crystals 13–14  
energy relaxation 294–6, 298, 308, 471  
envelope equations for sequential scattering 183–6  
equilibrium band diagrams 26–8  
equipartition approximation 205  
equivalent circuits, distributed FETs 557–62  
ergodic principle  
  and alloy scattering 171  
  and interface roughness scattering 168  
Esaki tunnel diode 128  
exchange correlation, and resonant tunneling 124  
  
Fermi energy/level 24, 29–30, 209  
  and charge control of 2DEG 265–9  
  Fermi’s golden rule 158, 541  
  and quantum wells 108  
  quasi-Fermi levels 34, 39–40, 536–7  
  and small electric field electron transport 293  
Fermi–Dirac distribution 202–3, 287, 542  
Fermi–Dirac function, and multi-band density of states 87–90  
Fermi–Dirac integral/statistics 27, 28  
Fermi–Dirac statistics in a 2DEG system 114–15  
Fibonacci superlattices and quasi-crystals 135–7, 138  
figures of merit, long- and short-channel MODFETs 342–3  
Fowler–Nordheim tunneling 119  
frequency of oscillation, maximum, long- and short-channel MODFETs 347  
Fukui equation for FET noise 591–3  
full-band structure effects, and resonant tunneling 124–7  
  
GaAs  
  band structure 15  
  bandgap, lattice parameter and electron affinity 20  
  material parameters 3, 459, 464  
  gain collapse, from thermal runaway in HBTs 669–70

- Gamma function, and electron transport in small electric fields 292
- GaP, bandgap, lattice parameter and electron affinity 20
- GaSb, bandgap, lattice parameter and electron affinity 20
- gate channel spacing 447, 450–1, 469, 490, 574
- gate metallization resistance 528, 531, 559–60, 574, 582–3, 605
- gate resistance/input resistance 527–62
  - AC performance and optimization 580–5
  - admittance analysis of a Schottky barrier with semiconductor surface states 536–40
  - Agilent EEsof Root FET Model 533
  - and gate width 529–32
  - interfacial gate resistance 532–4, 529
  - measurement and scaling 529–4
  - and necking 529–32, 604–5
  - Schottky barrier formation 534–5
  - and skin effect 528, 530
  - see also* interfacial tunneling calculation
  - application; interfacial tunneling resistance theory
- gate–source spacing 447, 574
- GCA (gradual-channel approximation)
  - MODFETs 318
  - MOSFET wave-equations, short channel case 384–7
- Ge
  - band structure 15
  - bandgap, lattice parameter and electron affinity 20
  - material parameters 3
- Glauber state
  - phonon distribution 155
  - and the uncertainty principle 106
- Grebene–Ghandhi MODFET model 323–31, 473
  - boundary conditions 326
  - short-gate MODFETs 473
- Green’s theorem 509, 544–5
- Gunn domain 474, 468
- Gunn effect/Gunn diode 307
- Hamiltonian
  - and crystals as masses and strings 139
  - electron–phonon couples 158
  - harmonic oscillator 153
  - Hermitian 71, 80–1, 83, 89, 196
  - interaction 157–8, 159, 161–2, 173
  - matrix elements for
    - heterostructure Hamiltonian 181
    - interaction Hamiltonian 181–3
    - Wannier functions 60
  - quantum wells 109
  - and the Schrödinger equation 54–5
  - time-dependent interaction 180
- HBT (heterojunction bipolar transistor) 44–6, 613–78
  - III–V processing technology 658–9, 660
  - III–V surfaces and the emitter base saddle-point 665–6
  - and abrupt heterojunctions 45
  - AlGaIn/GaN SHBT 655–6
  - and bandgap engineering 5–7
  - and conduction band discontinuity 45
  - delay times, 659–65
    - capacitive contribution to collector charge time 662–3
    - improving 661–5
    - origin and distribution 659–61
    - resistive contribution to collector charge time 662
  - design considerations 658
  - and doping 45
  - GaAs-based, advantages 442
  - GaAs transport properties 653–4
  - GaAsSb/InP DHBT 656
  - growth techniques 656–7
  - history and evolution 652–6
  - InGaP emitter GaAs base HBT 655
  - linearity aspects 45
  - MBE growth 44, 654–7
  - n–p–n HBTs 652–3
  - OMVPE growth technique 657
  - reliability, the beryllium diffusion problem 670–4
  - Richardson velocity 622
  - semiinsulating substrates 654
  - SiGe base HBT 442–3, 655
  - thermal considerations 666–70
    - gain collapse 669–70
    - thermal runaway 668–9
- HBT (heterojunction bipolar transistor) modeling
  - abrupt-junction 615–19, 621–3, 625–6, 629–32, 636–40, 644–6
  - Al mole fraction 617
  - applications and characteristics 443, 613–14
  - base widths in units of the mean free path 623
  - BTE (Boltzmann transport equation) direct solution 614–24
  - collector current density 623–4
  - compact model collector current 624–32
    - abrupt-junction 629–32
    - graded-emitter 625–29
  - compact models for cut-off frequencies 632–42
    - base–collector network 633, 641–2
    - extrapolated  $f_{\max}$  641–2
  - compact models for large-signal analysis 643–6
    - Ebers–Moll model 643–6
    - thermal considerations 646
  - compact models for regional delay 632–41
    - base delay 638–40
    - charge control method 632–5
    - collector delay 640–1
    - emitter delay 636–8
    - regional signal-delay expressions 635–41
  - conduction-band profiles 615
  - DDE-based simulators 627–29
  - distribution function components 618–20
  - electron concentration and velocity profiles 620–3
  - forward velocity profiles 622
  - injected and reflected electron fluxes at
    - emitter–base junction 616
  - microscopic modeling 614–24
  - tunneling probability 621
- HEMT (high-electron-mobility transistor)
  - applications and characteristics 442, 457
  - and bandgap engineering 6–7
  - and MODFETs 115

- HEMT (*cont.*)  
  process/manufacturability issues 600–6  
  *see also* MODFETs and PHEMTs  
Hermitian Hamiltonian 71, 80–1, 83, 89, 196  
heterojunction between two semiconductors with tight binding 70–1  
HFETs (heterostructure field-effect transistors), and bandgap engineering 5–7  
high electric field electron transport 286–310  
  Boltzmann equation/function 287  
  chordal mobility 299  
  energy balance equation 295–6  
  Gunn effect/Gunn diode 307  
  Joule effect 298  
  momentum conservation 301  
  negative differential mobility 303–8  
  non-uniform semiconductor case 296–9  
  stationary velocity overshoot in short devices 309–10  
  transient velocity overshoot in a time-varying field 308–9  
  two-valley model 299–303, 308, 448  
  uniform semiconductor case 294–6  
high speed technologies, table of comparisons 443–4  
hole bands, pseudomorphic materials/layers 4–5  
Houston functions/states/wave packet 102–4, 105–6, 223–6  
hybridization 11–12  
  
*I*–*V* characteristics  
  isothermal 418–20  
  and large-signal modeling 430–1  
  MODFET, quasi-two-dimensional model for 548–80  
  p–n heterojunctions 35–8  
    diode current calculation 36  
    excess carriers calculation 36–7  
    and the injection of majority carriers 38  
    and resonant tunneling structures 215  
    and thermionic emission effects 38–9  
    total depletion width 36  
  pulsed/transient 416–17, 418, 436–7  
impact ionization 477–8  
  in channel and gate tunneling, short-gate MODFETs 470–3  
impulse function 190, 197  
  and MSS (multiple-sequential scattering) 197  
InAs  
  band structure 15  
  bandgap, lattice parameter and electron affinity 20  
infrared response of quantum devices 251–62  
  optical absorption/emission coefficient 256–9  
  quantum cascade laser 259–62  
  and quantum transport coupling 254–6  
  simulation verification 257–9  
  wave guide modeling 252–3  
InP, bandgap, lattice parameter and electron affinity 20, 600, 678  
input resistance *see* gate resistance  
interface roughness 206  
  scattering from 165–9, 210–14  
interfacial gate resistance 529–34  
  and Schottky barrier formation 534–5  
  interfacial tunneling calculation application 550–7  
    AUDM 535, 551, 552, 554–6  
    barrier thickness effects 553  
    calculated interfacial gate resistance at DC and 50 GHz 551  
    Cowley–Sze’s vacuum picture 551–2, 554  
    equivalent circuits and *Y* parameters 557–62  
    interface parameter table for Vacuum IL, Oxide IL, MIGS and AUDM 552  
    MIGS 551, 552, 553–5  
    oxygen exposure problems 553  
    SGBFETs 553–4  
    Thomas–Fermi metal screening length 553  
interfacial tunneling resistance theory 540–50  
  Bardeen’s method 543–4  
  Cowley–Sze interfacial layer 546  
  Freeman and Dahlke’s model 549–50  
  general formalism for tunneling between metal and surface states 541–5  
  Green’s theorem 544–5  
  interfacial tunneling barrier 545–6  
  metal wave-function tail 546  
  surface-state wave-function 548–9  
  tunneling effective mass 546–8  
  tunneling resistance and capture cross-section 549–50  
intervalley scattering, LO phonons 165  
isothermal *I*–*V* characteristics 418–20  
  
Joule effect term 298  
  
knee current and voltage short-gate MODFETs 479  
Kurokawa’s definition 235  
  
laser, quantum cascade 259–62  
lattice structures *see* crystal and lattice structures  
lattice-matched systems 2–3  
LD (laterally diffused) MOSFETs  
  characterization 416  
  modeling 428  
LGLTB (linearly-graded low-temperature buffer) 600–2  
LNA (low noise amplifier) 589  
LO phonons, intervalley scattering 165  
  
MAG (maximum available (transducer power) gain), long- and short-channel MODFETs 344–5, 579  
manufacturability *see* process and manufacturability  
Maxwell–Boltzmann distribution 287–9  
MBE (molecular beam epitaxy) growth technique 1–7  
  application 7  
  bandgap engineering 5–7, 11–14  
  bandgap variation between GaAs and AlAs 2–3  
  Brillouin zone 10–11, 13–14, 15  
  HBT growth technique 656  
  hybridization 11  
  lattice-matched systems 2–3  
  limitations 7  
  morphological defects 7  
  pseudomorphic materials/layers 3–5, 6, 603  
  and quantum wells 106, 108  
  reciprocal lattice 9–11

- measurement at high frequencies 567–72
    - network analyzer (NWA) measurement 567–9
    - on-wafer testing 570–2
    - SOLT (short, open, load thru) calibration 421, 568, 572
  - MESFET *see* MODFETs
  - microwave data acquisition 421 *see also* network analyzer
  - microwave measurements of  $C$ – $V$  characteristics, RTDs 247–50
  - MIGS (metal-induced gap state) model 535–6, 538, 547, 551, 553–5
    - interface parameters for tunneling calculation 552
  - MMIC (monolithic microwave integrated circuit) 413, 445, 578
    - three-stage amplifier/process/manufacturability issues 600–1, 605
  - MOCVD (metal organic chemical vapor deposition) 7
  - modeling
    - an analytically manageable transport model 458–60
    - circuit simulations 436–8
    - electrothermal modeling 433–5
    - large-signal 426–33
      - charge 433
      - $I$ – $V$  characteristics 430–1, 460–70
    - LD MOSFETs 428
    - model formulation 426–8
    - non-quasi-static model 427
    - parasitic bipolar topologies 431–3
    - SOI MOSFETs 428
    - tensor product B-splines 428–30
  - physical-based models (vs. table-based) 414
  - power amplifier circuit simulations 437, 438, 561–2
  - power amplifiers 413–14, 477
  - pulsed  $I$ – $V$  circuit simulations 436–7
  - quasi-two-dimensional model for electrostatics and  $I$ – $V$  characteristics 460–80
  - small-signal 421–6
    - microwave data acquisition 421
    - parasitic deembedding 423–4, 425
    - topology 421–2
  - SPICE-based FET models 414
  - table-based modeling 414
  - thermal modeling 433–5
    - see also* device characterization
- MODFETs (modulation doped FETs) 115
- 2DEG concentration 333, 452
  - 2DEG gate charge control 449–58, 272–6
    - conduction-band diagram and gate 273, 451
  - doping concentrations 452
  - $DX$  trap phenomenon 25, 455–6
  - Thomas–Fermi screening 454
  - and the 2DEG structure 329
  - applications and characteristics 442–5
  - capacitor  $C$ – $V$  characteristics 275–9, 279–81
    - frequency dependence 278–9
    - and the Schottky junction modeling 279–81
  - and charge control with a Schottky junction 272
  - drain (or output) conductance 335, 514–15
  - extrinsic 337–8
  - GCA (gradual-channel approximation) 318
  - Grebene–Ghandhi model 323–31, 473
  - $I$ – $V$  model 314–38, 460–70
  - layout 315, 317
  - long- and short-channel 316–23
  - maximum short-circuited current gain 343
  - MOSFET saturation model 331–7
  - and MOSFETs 320–3
  - saturation and two-dimensional effects 323–37
  - $Y$  parameters *see*  $Y$  parameters
    - see also* HEMT (high-electron-mobility transistor); MOSFET; PHEMTs
- MODFETs (modulation doped FETs) high frequency performance 567–607
- current gain 576, 577
  - cut-off frequencies 576–80, 580–4
  - effective electron saturation velocity 580–1
  - gate metallization resistance 583, 585
  - gate-finger widths 583
  - interfacial gate resistance 585
  - measurement issues 567–72
  - power gain 577–80
  - procedure and parameters for calculating  $Y$  parameters 572–5
  - reverse modeling 606–7
    - see also* noise, noise figure and associated gain; process and manufacturability
- MODFETs, short-channel (short-channel modulation doped FETs) 384–411
- alternate equivalent circuit 395–6
  - charge conservation 408
  - charge-based representation 407–8
  - equivalent circuit for the
    - large-signal  $D$  internal node model 403–6
    - small-signal  $D$  internal node model 400–7
  - high-frequency performance 393–4, 395
- MAG (maximum available (transducer power) gain) 344–5
- maximum frequency of oscillation 347–50
  - maximum unity current-gain cut-off frequency 343, 347–50
  - model topology 409–10
- MSG (maximum stable gain) 345
- power gain resonances 393
- unilateral power gain of the wave-equation model 346–7
- see also* MOSFET wave-equations, short channel case
- MODFETs, long-channel (long-channel modulation doped FETs) 342–79
- MAG (maximum available (transducer power) gain) 344–5
  - maximum frequency of oscillation 347–50
  - maximum transconductance 343
  - maximum unity current-gain cut-off frequency 343, 347–50
  - MSG (maximum stable gain) 345
  - parasitic physical models 376, 378
  - unilateral power gain of the wave-equation model 346–7
    - see also* MOSFET wave-equations, long-channel case; MOSFET/MODFET long-channel large-signal model
- MODFETs, short-gate (short-gate modulation doped FETs) DC analysis 442–82

- MODFETs, short-gate DC analysis (*cont.*)
    - 2DEG gate charge control in a heavily dual pulse-doped MODFET structure 449–58
    - analytically manageable 2DEG transport model 458–60
    - DC modeling approach 446–8
    - high-field velocity-saturated region 466–70
    - impact ionization in the channel and gate tunneling 470–3
    - low-field gradual channel 461–4
    - quasi-two-dimensional model for electrostatics and  $I$ – $V$  characteristics 460–80
    - reliability 480–2
    - SBGFET semiconductor materials history 448–9
    - source, drain and contact resistances 464–6
    - see also* quasi-two-dimensional model for electrostatics and  $I$ – $V$  characteristics
  - MODFETs, short-gate (short-gate modulation doped FETs) velocity saturated, small-signal AC analysis 490–524
    - capacitances calculations 496–507, 520
    - conduction-induced currents and delays 507–19
    - conformal mapping for charge estimation 498–503
    - displacement currents 498–507
    - drain delays 491–4, 508, 514, 516–18
    - equivalent circuit discussion 491, 495, 519–21
    - equivalent circuit for intrinsic device 490–7
    - gate delay 496, 516, 518
    - gate-source capacitance 496, 505, 507
    - Green’s theorem 509
    - output (or drain) conductance 514, 515
    - saturation effects 493–5
    - transmission-line delay 514, 522
    - $Y$  parameter calculations 516, 519–24, 559–61
  - modulation doping 23–6
    - AlGaAs models 25
    - degenerate doping conditions 25, 452–5
    - history 449
    - and quantum wells 108
    - silicon as a amphoteric dopant 23–4
    - spike doping 24
  - mole fraction 21, 172, 449, 456–7, 466, 479, 602–3
    - HBTs 617, 639
  - molecular beam epitaxy 1–3, 7, 19, 23–4, 44, 106, 108, 129, 247, 600, 602–3, 654–7, 670–1
  - momentum conservation, high electric field transport 301
  - Monte-Carlo simulator 42, 458–9, 464, 510, 532, 661
  - MOSFET saturation model, channel opening 331–7
  - MOSFET wave-equations, long-channel case 350–65
    - alternative equivalent circuits for the intrinsic MODFET/MOSFET 363–5, 366
    - dimensionless representation of the  $y$  parameters 359
    - equivalent circuit 359–63
      - validity range of  $RC$  361–3
    - exact small-signal MOSFETs 351–6
      - gate and drain currents 353–6
      - space representation of MODFET wave-equation 535
    - frequency power series expansions of the  $y$  parameters 356–8
    - large signal 350–1
    - MOSFET wave-equations, short channel case 384–96
      - equivalent circuit of velocity saturated MOSFET 389–93
      - exact solution of velocity-saturated MOSFET 387–9
      - GCA (gradual-channel approximation) region 384–7
      - GCA/saturation boundary 386–7
    - MOSFET/MODFET long-channel large-signal model 365–76
      - charge conservation 373–6
        - in circuit simulators 374–6, 377
      - FET state equations verification 373–4
      - model derivation 366
      - $RC$  large signal model testing 367–72
    - MOSFET/MODFET short-channel large-signal model 396–7
      - velocity saturated
        - first-order non-quasi-static approximation 397–400
        - exact solution 398–400
  - MOSFETs, additional devices and features *see* MODFETs
  - MSG (maximum stable gain), long- and short-channel MODFETs 345, 580
  - MSS (multiple-sequential scattering) 181, 185, 188
    - and ISS Hamiltonian system 199–201
    - backward transmission coefficient 200
    - detailed balance 198–204
    - Fermi–Dirac distribution 201–3
    - forward transmission coefficient 199
    - and the impulse function 197
    - and LO phonon scattering 194
  - MSS algorithm and scattering processes 190–3
  - occupation number 204
  - Pauli exclusion 194, 202, 204
  - and self-energy 189
  - time reversal 199–201
- multi-band density of states 86–91
    - and the Fermi–Dirac function 87–90
    - partial multi-band density 90
  - NDC (negative differential conductivity) region, RTDs 244
  - NEGF (non-equilibrium Green function) 215–16
  - network analyzer (NWA) measurement and calibration 567–71
  - Newman functions 98–9
  - noise, noise figure and associated gain 584–600
    - correlation admittance 594
    - and DBS (direct broadcast satellite) applications 593
    - effective noise conductance 594
    - effective noise resistance 594
    - equivalent representations of an FET with noise 587
    - formalism for noise figure and power gain 593–5
    - Fukui equation 591–3
    - high-frequency noise sources 586
    - LNA (low noise amplifier) 589
    - low-frequency noise 586
    - MODFET noise analysis 595–600
    - noise figure  $F$  (total noise figure) 588–9



- noise, noise figure and associated gain (*cont.*)
  - Norton's theorem 586
  - PHS (Pucel, Haus and Statz) noise model/analysis 589–91
  - Pospieszalski's thermal model 591–3
  - Rollett's maximum available gain 595
- occupation number 204
- OEIC (optoelectronics integrated circuits) 7
- OMVPE (organometallic vapor phase epitaxy) HBT growth technique 657
- on-wafer testing 570–2
- optical absorption, and infrared response 256–9
- optical phonons 152
  - polar scattering by 161–2
- output conductance 514, 572–3
- oxide IL, interface parameters for tunneling calculation 552
- parasitic bipolar topologies, modeling 431–2, 433
- parasitic deembedding 422–4, 425
- Pauli exclusion principle 131–3, 194, 202, 204
- periodic superlattices 131–3
- PHEMTs (pseudomorphic HEMTs)
  - applications and characteristics 442, 444, 457, 474, 477, 531–2, 589
  - history 449
- phonons and phonon scattering 148–60
  - acoustic phonons, deformation potential scattering by 162–4
  - and the Bose–Einstein distribution 156–7
  - and the conservation of energy and momentum 153
  - and creation and annihilation operators 154
  - and the Einstein model 152
  - electron and lattice Hamiltonian 157–8
  - and the Fermi golden rule 158
  - Glauber state 155
  - interaction Hamiltonian 157–8, 159, 161–2
  - intervalley scattering by LO phonons 165
  - and the lattice displacement operator 155
  - optical phonons 152
  - particle nature of 152–3
  - phonon states 155
  - phonon-assisted resonant tunneling 179
  - polar scattering by optical phonons 161–2
  - quantum analysis of crystal vibration 152
  - scattering analysis 150–1
  - semiclassical phonon model 159–60
  - spontaneous and stimulated emissions 157–9
- physics-based (vs. table-based) models 414
- piezoelectric effect 29
- pinch-off voltage, 2DEGs 274–5
- Poisson equation
  - and resonant tunneling 122
  - in a spatially-varying heterostructure 28
- polar scattering 204–5, 208–9, 210
- power amplifiers
  - circuit simulation 437, 438, 561–2
  - modeling 413–14
- process and manufacturability 600–6
  - gate process 463, 603–5
  - HEMT (high-electron-mobility transistor) 600
  - and LGLTB 600–2
- misfit dislocations 601
- MMIC (monolithic microwave integrated circuit)
  - three-stage amplifier 600–1
- threshold control 603
- yield considerations 602–3
- pseudomorphic materials/layers 3–5, 6
  - light/heavy-hole bands 4–5
- pulsed  $I$ – $V$ 
  - characteristics 416–17, 418
  - circuit simulations 436–7
- punch-through, short-gate MODFETs 470, 474, 477
- quantum cascade laser 259–62
- quantum properties of electrons 54–68
- quantum transport coupling, and infrared response 254–6
- quantum wells 106–15
  - 2DEG 110–15
  - arbitrary shapes 109
  - density of states
    - in  $E$  space 113–14
    - $k$  space 111–13
  - eigenstate in triangular wells 108–9
  - electric field induced 108–9
  - Fermi level alignment 108
  - Fermi–Dirac statistics in a 2DEG system 114–15
  - full-band structure effects 110
  - Hamiltonian 109
  - and MBE growth technique 106, 108
  - rectangular 107–8
- quasi-crystals and Fibonacci superlattices 135–7, 138
- quasi-two-dimensional model for electrostatics and  $I$ – $V$  characteristics, short-gate MODFETs 460–80
  - avalanche breakdown 471–2
  - continuity equation for channel current 460–1
  - gate tunneling 472–3
  - Grebene–Ghandi problem 473
  - Gunn domain 474
  - high-field velocity-saturated region 466–70
  - impact ionization 470–2, 477
  - intrinsic transconductance versus gate length 476–7
  - knee current 479
  - low-field gradual channel 461–4
  - output conductance 470
  - punch-through 470, 474, 477
  - velocity saturation 474
- radiation coupling with an external modulated electric field 222–8
- random superlattices 133–5
- reciprocal lattice 9–11
  - vector 10
- reliability
  - the beryllium diffusion problem for HBTs 670–4
  - short-gate MODFETs 480–2
- resistances
  - 2DEG full channel sheet resistance 529, 574
  - Agilent EEsof Root FET Model, gate resistance 533
  - contact resistances 465–6
  - effective noise resistance 594

- resistances (*cont.*)
  - gate metallization resistance 583
  - necking, and gate resistance 529–30
  - source, drain resistances 464–5
  - see also* gate resistance/input resistance; interfacial gate resistance; interfacial tunneling resistance theory
- resonant tunneling 115–29
  - and charge distribution inside the well 121–3
  - double-barrier system/structure 115–19
  - and exchange correlation 124
  - full-band structure effects 124–7
  - high-frequency and high-speed response 128
  - RITDs 128–9
  - and scattering induced broadening 124
  - and three-dimensional electron gas concentration 120
  - time-dependent theory 228–32
  - tunneling current 119–21
- reverse modeling 606–7
- Richardson constant/velocity 39, 280, 622
- RITDs (resonant interband tunneling diodes) 128–9
- Rollett’s maximum available gain 579, 595
- RTDs (resonant tunneling diodes) 44, 178
  - application of scattering-assisted tunneling theory 207–15
  - and bandgap engineering 6–7
  - capacitances 238–41
  - conductances 237–8
  - DC and AC self-consistent analysis 236–7
  - DC bias instabilities 250–1
  - high-frequency response 241–7
  - I*–*V* characteristics 247, 248, 249, 250
  - maximum frequency 245–6
  - microwave measurements of *C*–*V* characteristics 247–50
  - NDC (negative differential conductivity) region 244
  - self-consistent solution 233–7
  - small-signal response without self-consistent potential 232–3
  - and time-dependent tunneling theory 232–3
- S*-matrix representation 195–8
- SBGFET (III–V Schottky-barrier gate FET)
  - applications and characteristics 442–5
  - interfacial tunneling barrier considerations 553–4, 557
  - materials history 448–9
  - modeling 446–8
  - parasitic gate resistance 536, 533–4
- scattering assisted tunneling *see* tunneling, scattering assisted
- scattering induced broadening, and resonant tunneling 124
- scattering processes 148–74
  - ISS (single-sequential scattering) 194–5, 197
  - acoustic phonon deformation scattering 162–4
  - AL (alloy scattering) 206–7
  - alloy scattering 169–72
  - backscattering 174
  - coupling functions 204–7
  - deformation potential LO phonon scattering 205–6
  - elastic scattering 185
  - electron–electron scattering 172–4
  - envelope equations for scattering 183–6
  - $\Gamma$ –*X* intervalley scattering 209–13
  - interface roughness 165–9, 206, 210–14
  - LO phonon intervalley scattering 165
  - optical phonon polar scattering 161–2
  - optical phonon scattering 185
  - phonons and phonon scattering 148–60, 185
  - polar scattering 204–5, 208–9, 210
  - scattering analysis 150–1
  - three-dimensional 178–80
  - see also* tunneling, scattering assisted
- Schottky barrier
  - admittance analysis with semiconductor surface states 536–40
  - and interface gate resistance 534–5
  - various models 535, 550–7
  - see also* gate resistance/input resistance; interfacial tunneling calculation application; interfacial tunneling resistance theory; SBGFET
- Schottky junction, and 2DEGs 272–5
- Schrödinger equation 54–5
  - and the conservation of particles 72–3
  - and coupling quantum transport with infrared radiation 254
  - and resonant tunneling 122
  - and semiclassical scattering 181
  - and time dependent tunneling theory 229
  - and tunneling between metal and surface states 541
- self energy, and scattering-assisted tunneling 188–90
- semiconductor material parameter tables 47, 48
- semiinsulating substrates 654, 674
- SHBT (single-heterojunction bipolar transistor) 655–6
- Si
  - as an amphoteric dopant 23–4
  - band structure 15
  - bandgap, lattice parameter and electron affinity 20
- simulations *see* modeling
- skin effect, and gate resistance 528, 530, 574
- small electric field electron transport 290–4
  - Boltzmann equation 290–2
  - Fermi level 293
  - Gamma function 292
  - non-uniform semiconductor case 292–4
  - uniform semiconductor case 290–2
- SOI (silicon on insulator) MOSFETs, modeling 427–8
- SOLT (short, open, load thru) calibration of NWA 421, 568, 572
- source resistances 464–6
- spatially-varying crystals 68–79
  - electron particle current (flux) 72–5
  - heterojunction between semiconductors 70–1
  - matching theory 76–8
  - three-dimensional effects 78–9
- spatially-varying semiconductors 19–26
  - modulation doping 23–6
  - semiconductor alloys 20–3
- SPICE-based FET models 414
- spike doping 24
- Stark states and the Wannier ladder 98–102, 105
  - eigenstate solutions 98–101
  - Zener resonant tunneling 101–2, 103



- superlattices 129–38
  - and Anderson localization 135
  - application 129
  - and the Bloch oscillator 132–3
  - periodic superlattices 131–3
  - quasi-crystals and Fibonacci superlattices 135–7, 138
  - random 133–5
  - superlattice axis 19
  - and the Wannier ladder 132, 134
- surface-state wave-function, and interfacial tunneling resistance 548–9
- table-modeling 414
- TEGFET (two-dimensional electron gas FET)
  - and MODFETs 115
  - see also* MODFETs
- tensor product B-splines 428–30
- terraces and terrace density 166–9
- thermal considerations, HBTs 666–70
- thermal modeling 433–5
- thermionic models 38–42
  - excess minority-carrier concentration 41
  - and the  $I$ – $V$  diode characteristic 41
  - and the quasi-Fermi level 39–40
  - and the Richardson constant 39
- Thomas–Fermi screening 454, 455, 553
- three-dimensional band structure model, and quantum wells 111
- three-dimensional scattering 178–80
- threshold voltage, 2DEGs 274–5, 450
- time-dependent tunneling theory 228–32 tested by
  - application to RTD 232–3
- time-reversal 196
- time-varying quantum systems 221–2
- TM mode, and infrared response 253
- total particle current, definition 73–4
- TPS (tensor product B-splines) 428–30
- translation invariance, Wannier functions 60
- translation operator, and electron in a periodic potential 55–6
- transmission line delay 514–16, 522, 568
- transparency wave-matching technique for two-band system 82–3
- tunneling *see* interfacial tunneling calculation
  - application; interfacial tunneling resistance theory; resonant tunneling; RTDs (resonant tunneling diodes); tunneling, scattering assisted
- tunneling, scattering assisted 177–216
  - and ballistic transport 177
  - envelope equations for sequential scattering 183–6
  - and the Hermitian Hamiltonian system 196
  - matrix elements for the
    - heterostructure Hamiltonian 181
    - interaction Hamiltonian 181–3
  - NEGF formalisms 215–16
  - RTD (resonant tunneling diode) 178
  - scattering-parameter representation 194–8
  - self-energy 188–90
  - semiclassical scattering picture 180–1
  - theory of 180–6
  - transmission coefficient 186–8
  - see also* MSS
- two-dimensional electron gas *see* 2DEG
- two-dimensional model for electrostatics and  $I$ – $V$  characteristics *see* quasi-two-dimensional model
  - two-valley model, high-field transport 299–303, 308
- vacuum IL, interface parameters for tunneling calculation 552
- valence band 6, 21–2
  - valence band offsets 27
- Vegard’s law 21
- velocity saturation short-gate MODFETs 474
- virtual-crystal approximation/average potential 20, 169
- Wannier expansion, and semiclassical scattering 181
- Wannier functions 58–64
  - and 2DEG as a function of the Fermi level 265–7
  - and the Bloch function/state 64, 67
  - and the Bloch theorem 60, 65–6
  - bra-ket notation 61
  - completeness 60
  - convergence 60
  - eigenstate solutions 62, 66
  - envelope function 75
  - flat-band case 63
  - generalized 69–70
  - Hamiltonian derivation 61–2
  - Hamiltonian matrix elements 60
  - heterojunction between semiconductors 70–1
    - and interface roughness scattering 166
    - and multi-band density of states 88
  - normalization and orthogonality 60
  - properties table 70
  - three-dimensional crystal 64–8
  - three-dimensional Wannier recurrence equation 79
  - and time-dependent tunneling theory 229–30
  - translation invariance 60
    - proof of 60–1
  - Wannier recurrence equation 61–3
- Wannier ladder 98–101
  - and superlattices 132
- Wannier ladder energy spacing 222
- Wannier multi-band tridiagonal system 79–86
  - effective-mass wave-matching for two-band system 81–4
- full-band model comparison 84–6
- Hamiltonian 79–80
- Hermiticity of the Hamiltonian 80–1, 83, 89
- transparency wave-matching technique 82–3
- Wannier recurrence equation 98–101, 222
  - and double-barrier systems 115–19
- Wannier state, and coupling quantum transport with infrared radiation 254
- wave guide modeling, and infrared response 252–3
- $Y$  parameters 516
  - calculation procedures and parameters recap 572–5
  - equivalent circuit, gate resistance and Schottky barrier interface 557–62
  - measurement problems 567–8

688 Index

<i>Y</i> parameters ( <i>cont.</i> )	Zener oscillations 227–8
MOSFET wave equations, long-channel case	coherent and squeezed 105–6
356–8, 359	Zener resonant tunneling 101–2, 103
short-gate MODFETs 519–24	zinc-blende crystal structure 8–11